

PN2907A

Preferred Device

General Purpose Transistor

PNP Silicon



ON Semiconductor™

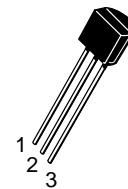
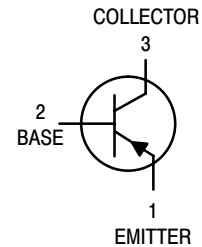
<http://onsemi.com>

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–60	Vdc
Collector–Base Voltage	V_{CBO}	–60	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

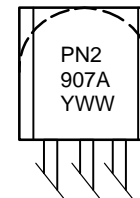
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W



TO-92
CASE 29
STYLE 1

MARKING DIAGRAM



PN2907A = Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
PN2907A	TO-92	5000 Units/Box
PN2907ARLRA	TO-92	2000/Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 1.) (I _C = –10 mA _{dc} , I _B = 0)	V _{(BR)CEO}	–60	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = –10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	–60	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = –10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	–5.0	–	V _{dc}
Collector Cutoff Current (V _{CE} = –30 V _{dc} , V _{EB(off)} = –0.5 V _{dc})	I _{CEX}	–	–50	nA _{dc}
Collector Cutoff Current (V _{CB} = –50 V _{dc} , I _E = 0) (V _{CB} = –50 V _{dc} , I _E = 0, T _A = 150°C)	I _{CBO}	– –	–0.01 –10	μA _{dc}
Base Current (V _{CE} = –30 V _{dc} , V _{EB(off)} = –0.5 V _{dc})	I _B	–	–50	nA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = –0.1 mA _{dc} , V _{CE} = –10 V _{dc}) (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc}) (I _C = –10 mA _{dc} , V _{CE} = –10 V _{dc}) (I _C = –150 mA _{dc} , V _{CE} = –10 V _{dc}) (Note 1.) (I _C = –500 mA _{dc} , V _{CE} = –10 V _{dc}) (Note 1.)	h _{FE}	75 100 100 100 50	– – – 300 –	–
Collector–Emitter Saturation Voltage (Note 1.) (I _C = –150 mA _{dc} , I _B = –15 mA _{dc}) (I _C = –500 mA _{dc} , I _B = –50 mA _{dc})	V _{CE(sat)}	– –	–0.4 –1.6	V _{dc}
Base–Emitter Saturation Voltage (Note 1.) (I _C = –150 mA _{dc} , I _B = –15 mA _{dc}) (I _C = –500 mA _{dc} , I _B = –50 mA _{dc})	V _{BE(sat)}	– –	–1.3 –2.6	V _{dc}

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (Notes 1. and 2.), (I _C = –50 mA _{dc} , V _{CE} = –20 V _{dc} , f = 100 MHz)	f _T	200	–	MHz
Output Capacitance (V _{CB} = –10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	8.0	pF
Input Capacitance (V _{EB} = –2.0 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	–	30	pF

SWITCHING CHARACTERISTICS

Turn–On Time	(V _{CC} = –30 V _{dc} , I _C = –150 mA _{dc} , I _{B1} = –15 mA _{dc}) (Figures 1 and 5)	t _{on}	–	45	ns
Delay Time		t _d	–	10	ns
Rise Time		t _r	–	40	ns
Turn–Off Time	(V _{CC} = –6.0 V _{dc} , I _C = –150 mA _{dc} , I _{B1} = I _{B2} = 15 mA _{dc}) (Figure 2)	t _{off}	–	100	ns
Storage Time		t _s	–	80	ns
Fall Time		t _f	–	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

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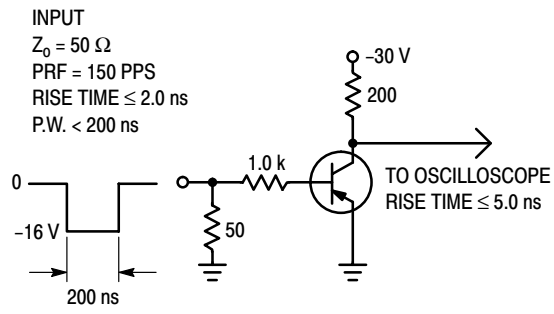


Figure 1. Delay and Rise Time Test Circuit

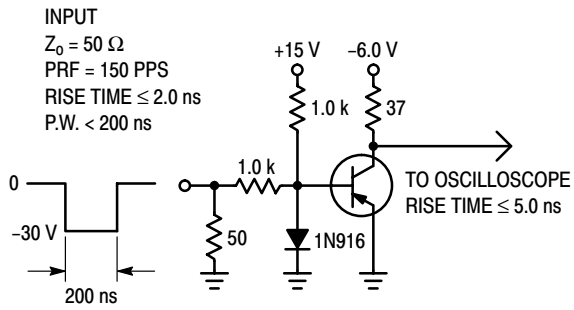


Figure 2. Storage and Fall Time Test Circuit

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TYPICAL CHARACTERISTICS

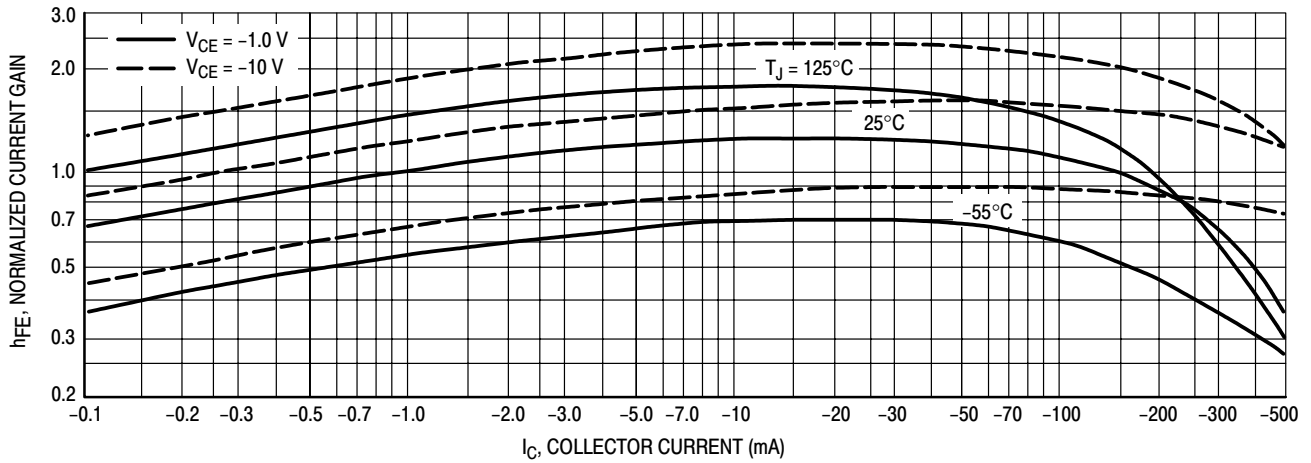


Figure 3. DC Current Gain

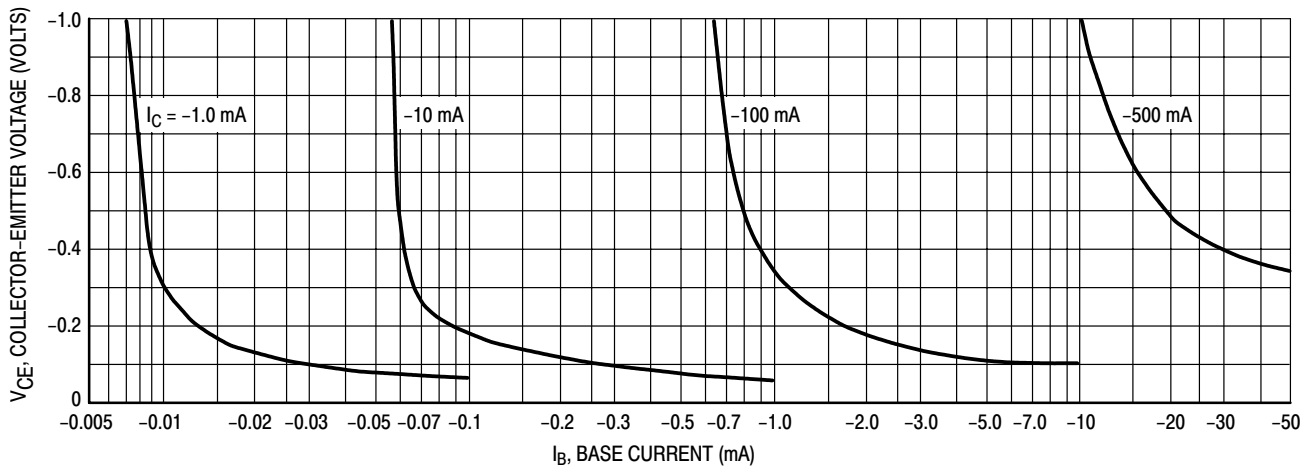


Figure 4. Collector Saturation Region

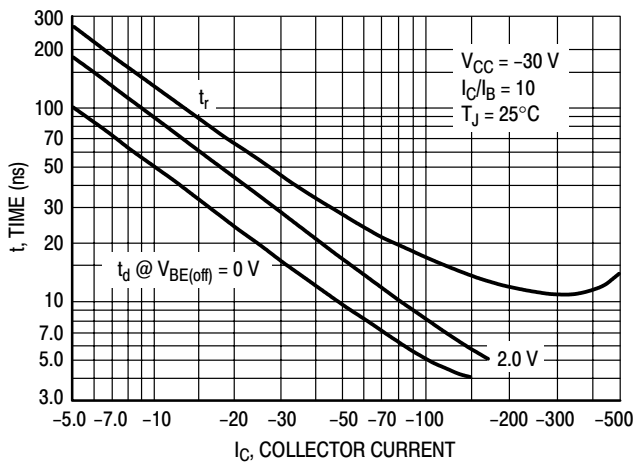


Figure 5. Turn-On Time

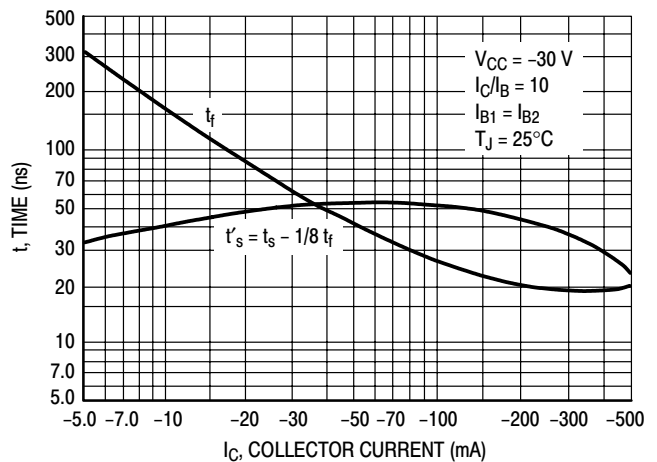


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

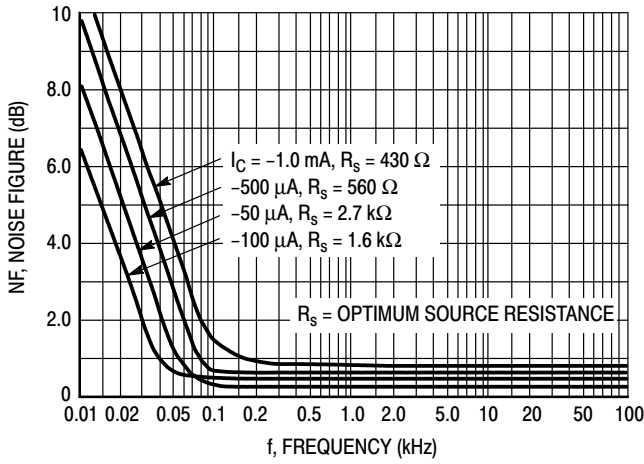


Figure 7. Frequency Effects

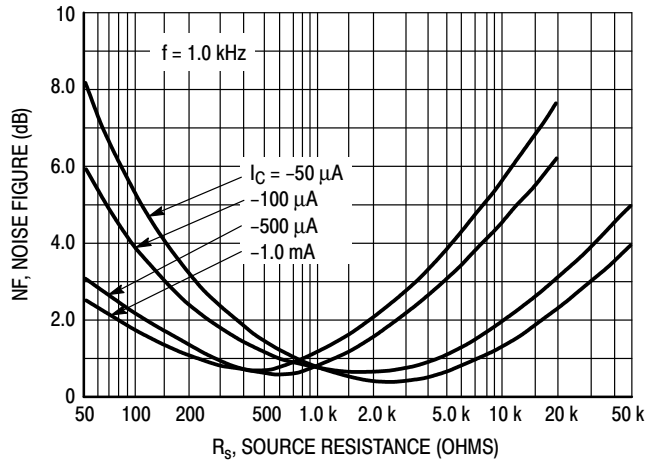


Figure 8. Source Resistance Effects

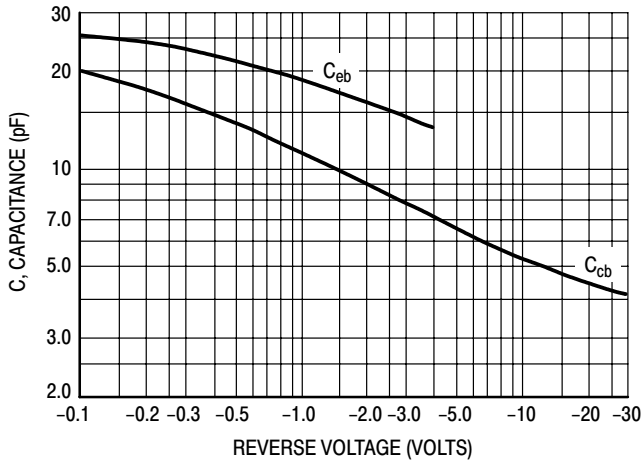


Figure 9. Capacitances

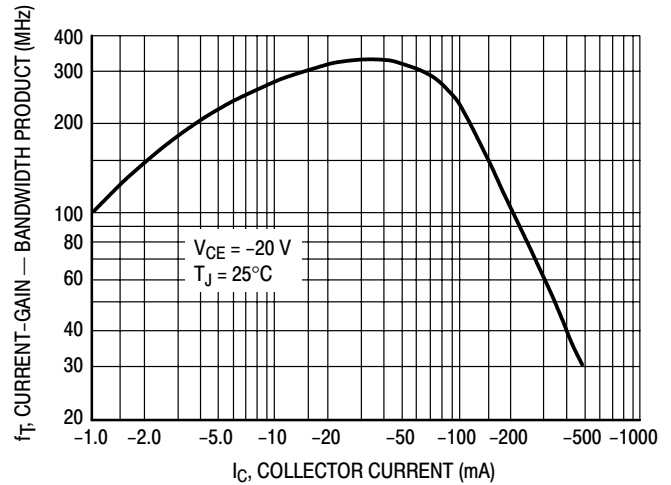


Figure 10. Current-Gain — Bandwidth Product

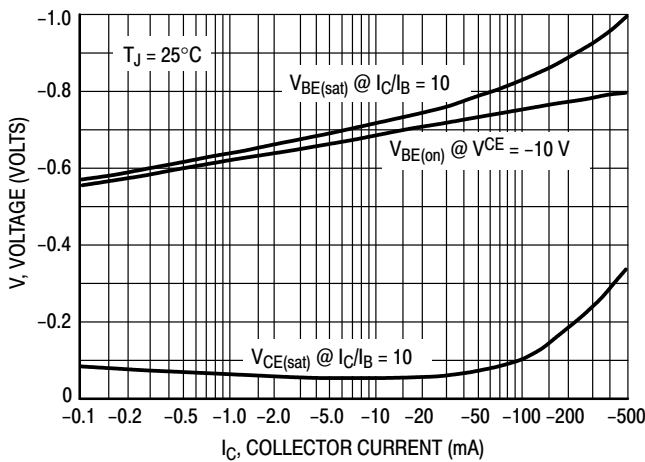


Figure 11. "On" Voltage

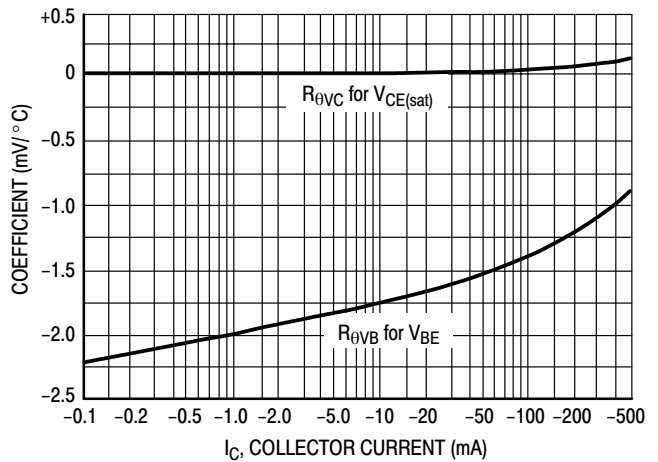
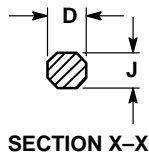
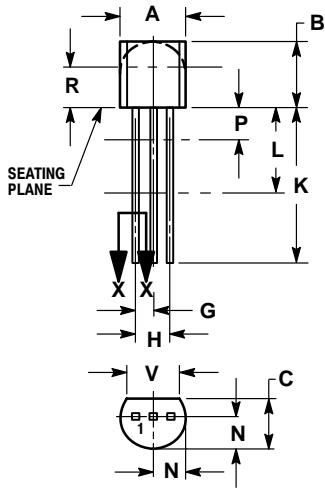


Figure 12. Temperature Coefficients

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PACKAGE DIMENSIONS

TO-92
TO-226AA
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

- PIN 1. EMITTER
2. BASE
3. COLLECTOR

Notes

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